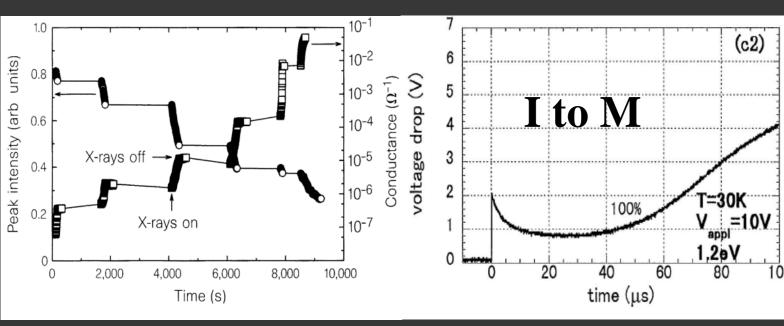
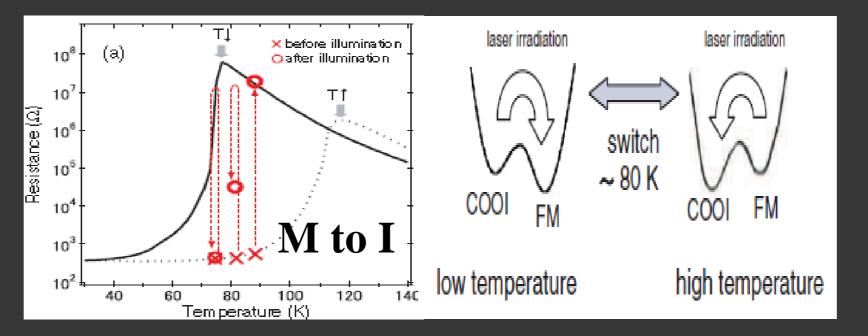
Visualization of a stable intermediate phase in photoinduced metal-to-insulator transition in manganites

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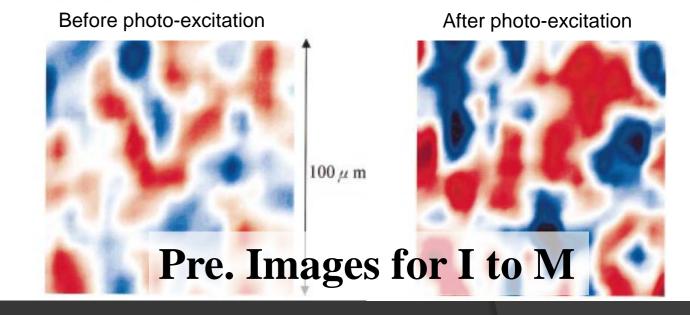
Introduction



V. Kiryukhin et al. Nature **386**, 813 (1997).K. Miyano et al. Phys. Rev. Lett. **78**, 4257 (1997).



N. Takubo et al. Phys. Rev. Lett. 101, 177403 (2008).



Y. Okimoto et al. Appl. Phys. Lett. 80, 1031 (2002).

Results

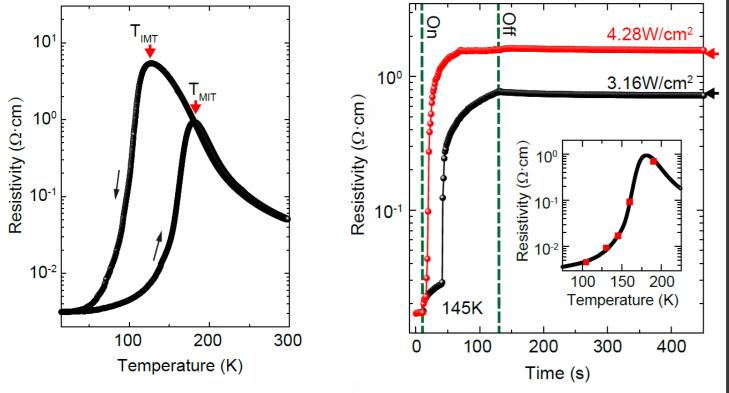
I. Transport Properties

II. MFM images (The COI phase increases as well as the *"white" phase* !)

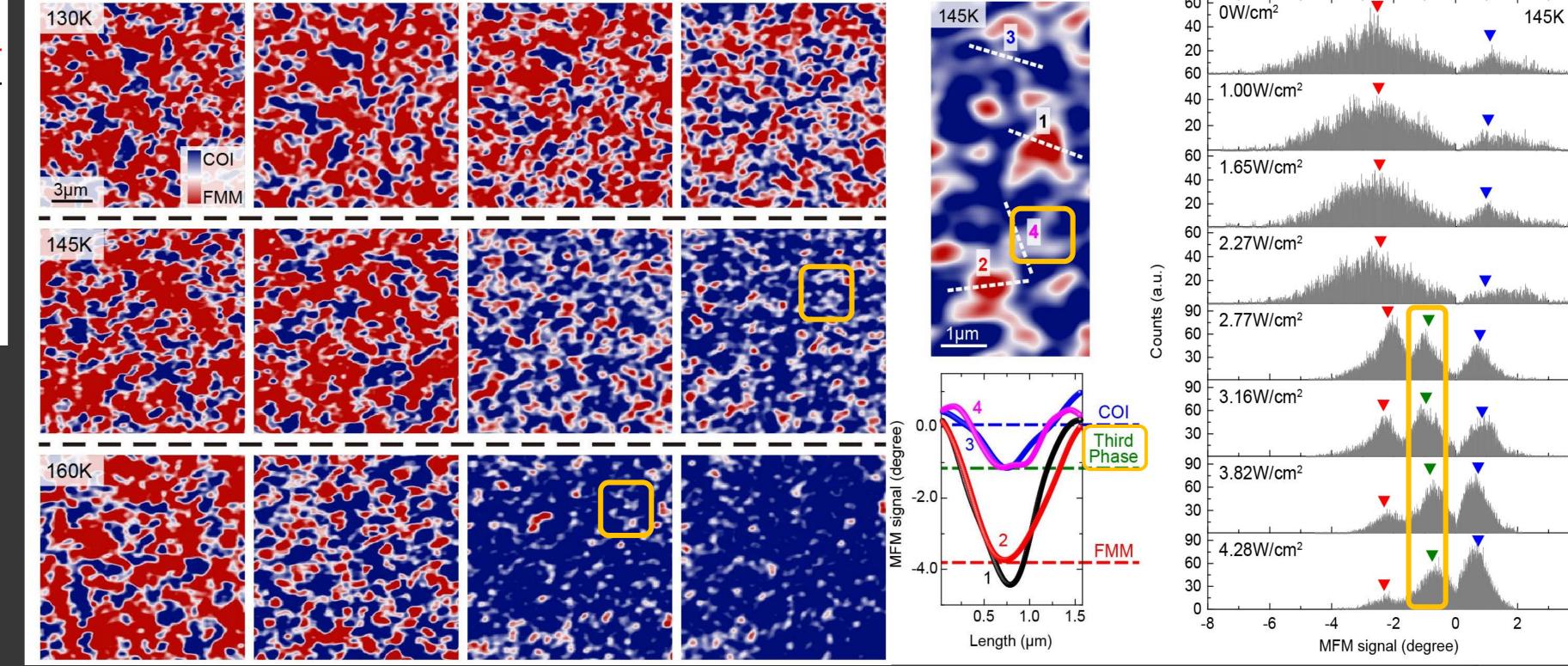
0W/cm² 2.23W/cm² 3.16W/cm²

m² 4.28W/cm²

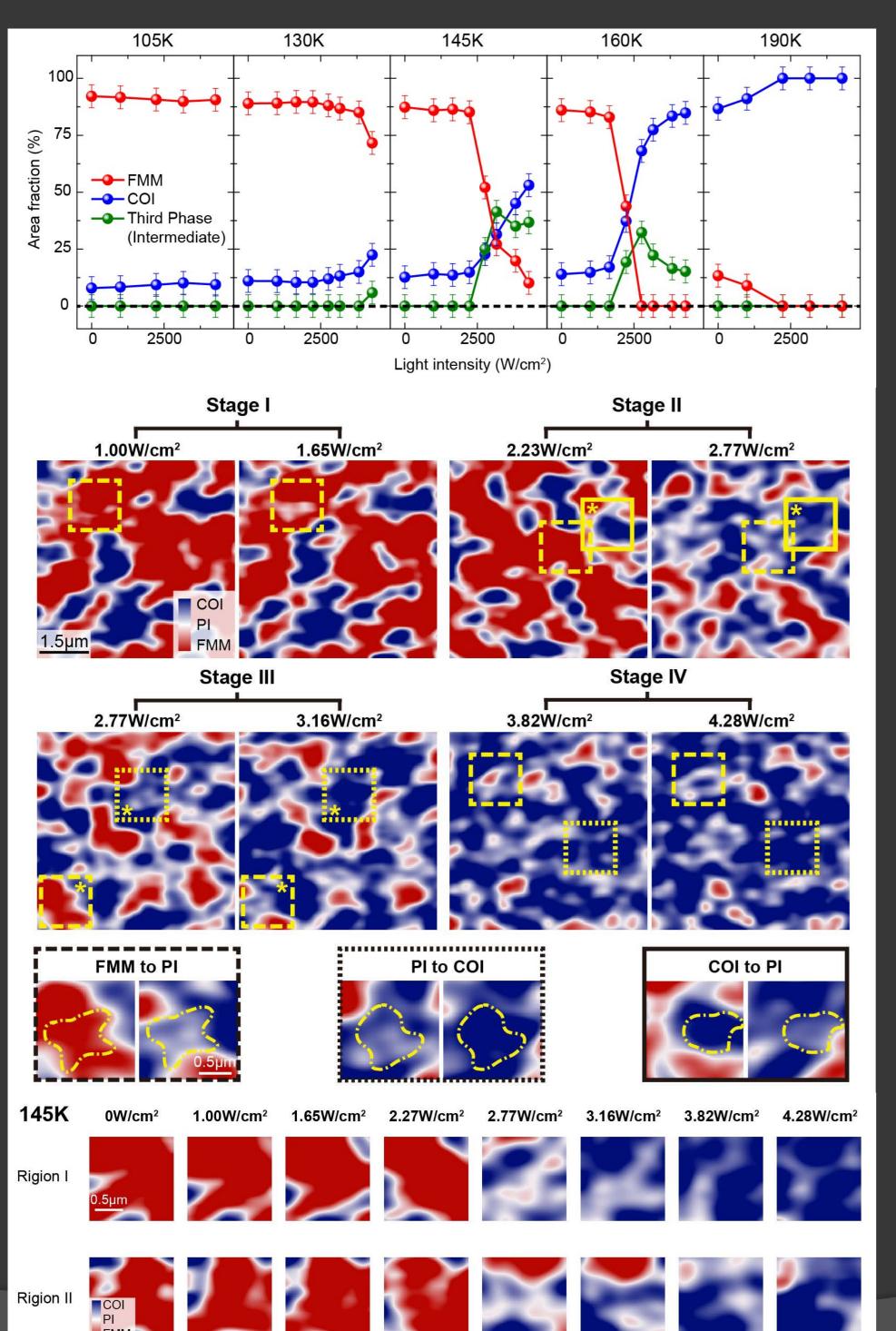
b -8 -6 -4 -2 0 2



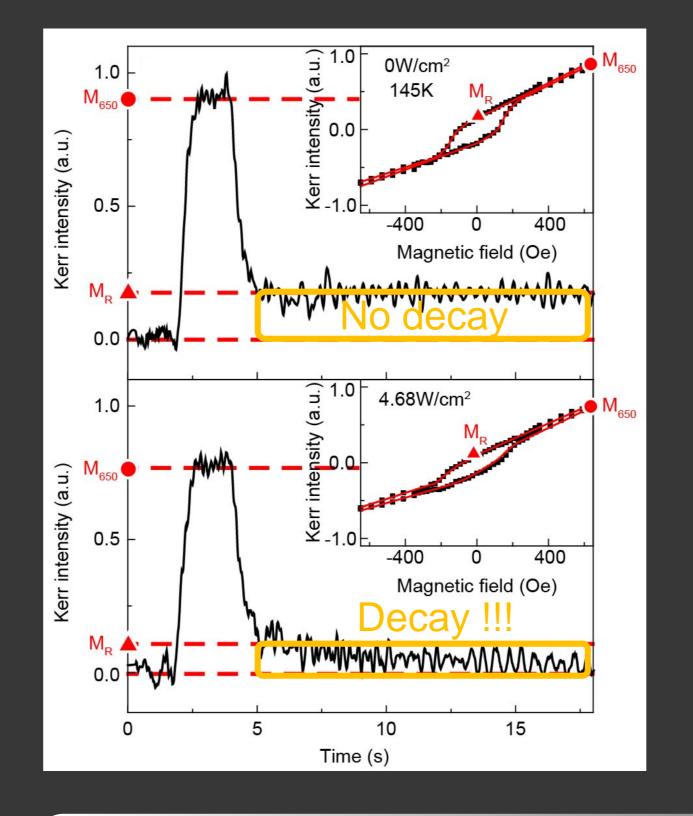
Sample : 40 nm La_{0.325}Pr_{0.3}Ca_{0.375}MnO₃ on LAO(001) Laser : 1.3 ns 2 kHz 532 nm MFM: Atto Cube commercial set-up



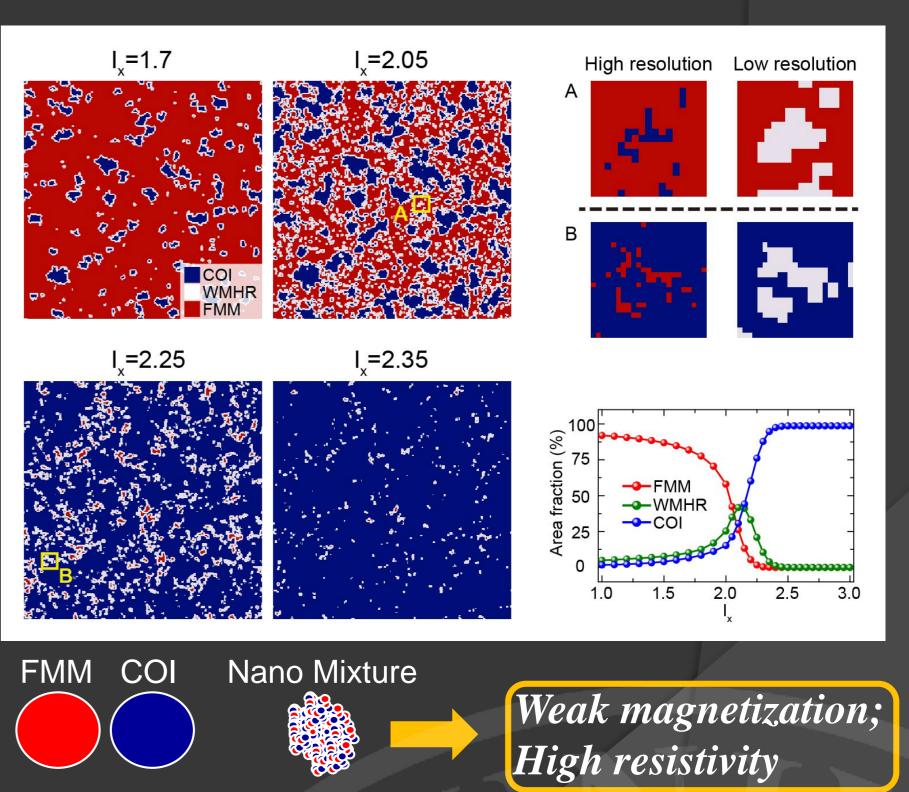
III. The mediatory role of the third (intermediate) phase



IV. The nanoscale mixing nature of the third phase (MOKE)



V. The nanoscale mixing nature of the third phase (Numerical calculation)



Conclusion

- A stable intermediate phase emerges and mediate photo-induced IMT in manganites.
- The *submicron* intermediate phase is formed *collectively* by the *nanoscale* FMM and COI phases, distinctive from the previously identified submicron FMM and COI phases.
- Two distinct phase separation length scales (nano and submicron) exists simultaneously in one system.
- The weak magnetization and high resistivity of the intermediate phase is the inevitable results of its nanoscale mixture nature.



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for Nanoelectronics Devices and Quantum Computing, Fudan University, Shanghai 200433, China 6 Collaborative Innovation Center of Advanced Microstructures, Nanjing 210093, China